

## HIGH VOLTAGE SWITCHING APPLICATIONS

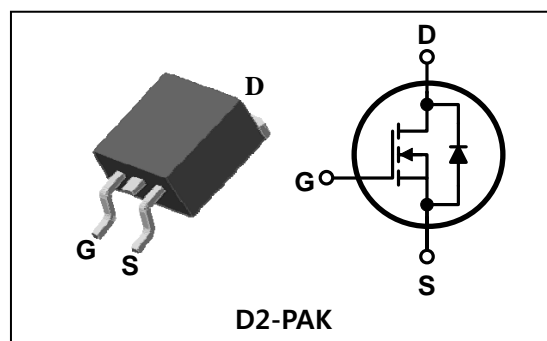
### Features

- High Voltage :  $BV_{DSS}=200V(\text{Min.})$
- Low  $C_{RSS}$  :  $C_{RSS}=55pF(\text{Typ.})$
- Low gate charge :  $Qg=22nC(\text{Typ.})$
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=0.17\Omega(\text{Max.})$

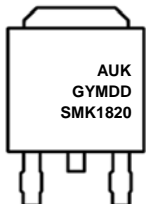
### Ordering Information

Type No.	Marking	Package Code
SMK1820D2	SMK1820	D2-PAK

### PIN Connection



### Marking Diagram

	Column 1 : Manufacturer
	Column 2 : Production Information e.g.) GYMDD
	- . G : Factory management code - . YMDD : Date Code (year, month, date)
	Column 3 : Device Code

### Absolute maximum ratings ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	$V_{DSS}$	200	V	
Gate-source voltage	$V_{GSS}$	$\pm 30$	V	
Drain current (DC) *	$I_D$	$T_C=25^\circ\text{C}$	18	A
		$T_C=100^\circ\text{C}$	11.4	A
Drain current (Pulsed) *	$I_{DM}$	72	A	
Power dissipation	$P_D$	100	W	
Avalanche current (Single) ②	$I_{AS}$	18	A	
Single pulsed avalanche energy ②	$E_{AS}$	453	mJ	
Avalanche current (Repetitive) ①	$I_{AR}$	18	A	
Repetitive avalanche energy ①	$E_{AR}$	13.9	mJ	
Junction temperature	$T_J$	150	$^\circ\text{C}$	
Storage temperature range	$T_{stg}$	-55~150		

\* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit
Thermal resistance	Junction-case	-	1.25	$^\circ\text{C}/\text{W}$
	Junction-ambient	-	62.5	

## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit	
Drain-source breakdown voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	200	-	-	V	
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> =V <sub>GS</sub>	2.0	-	4.0	V	
Drain-source cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =200V, V <sub>GS</sub> =0V	-	-	1	μA	
		V <sub>DS</sub> =160V, T <sub>C</sub> =125°C	-	-	10		
Gate leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V	-	-	±100	nA	
Drain-source on-resistance ④	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =9.0A	-	0.14	0.17	Ω	
Forward transfer conductance ④	g <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =9.0A	-	10.5	-	S	
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V f=1 MHz	-	942	1240	pF	
Output capacitance	C <sub>oss</sub>		-	227	310		
Reverse transfer capacitance	C <sub>rss</sub>		-	55	71		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =100V, I <sub>D</sub> =18A R <sub>G</sub> =25Ω	-	15	-	ns	
Rise time	t <sub>r</sub>		-	130	-		
Turn-off delay time	t <sub>d(off)</sub>		③④	-	135		-
Fall time	t <sub>f</sub>		-	105	-		
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> =160V, V <sub>GS</sub> =10V I <sub>D</sub> =18A	-	22	28	nC	
Gate-source charge	Q <sub>gs</sub>		③④	-	6.6		-
Gate-drain charge	Q <sub>gd</sub>		-	-	7.2		-

## Source-Drain Diode Ratings and Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

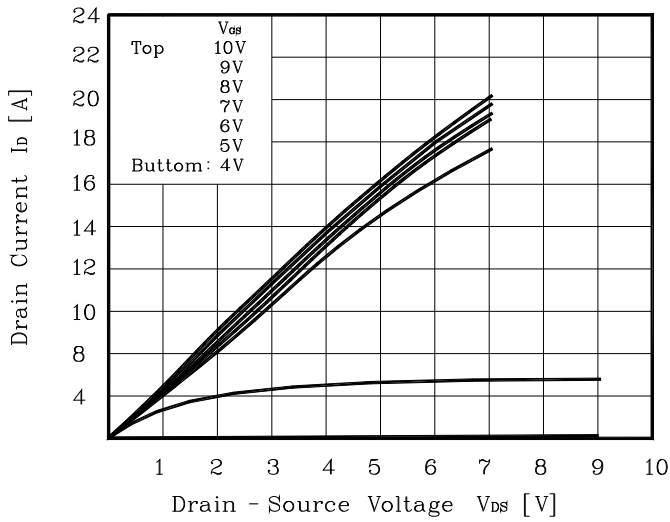
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I <sub>S</sub>	Integral reverse diode in the MOSFET	-	-	18	A
Source current (Pulsed) ①	I <sub>SM</sub>		-	-	72	
Forward voltage ④	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =18A	-	-	1.4	V
Reverse recovery time	t <sub>rr</sub>	I <sub>S</sub> =18A, V <sub>GS</sub> =0V dI <sub>F</sub> /dt=100A/μs	-	208	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	1.63	-	μC

Note ;

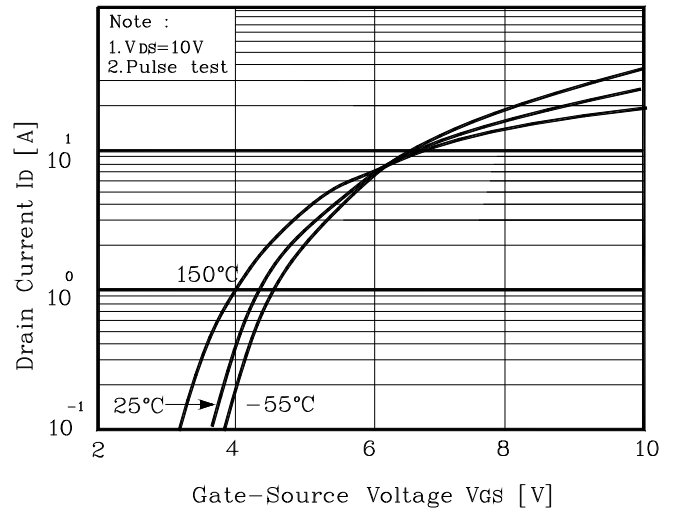
- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② L=2.1mH, I<sub>AS</sub>=18A, V<sub>DD</sub>=50V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C
- ③ Pulse Test : Pulse width≤300μs, Duty cycle≤2%
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

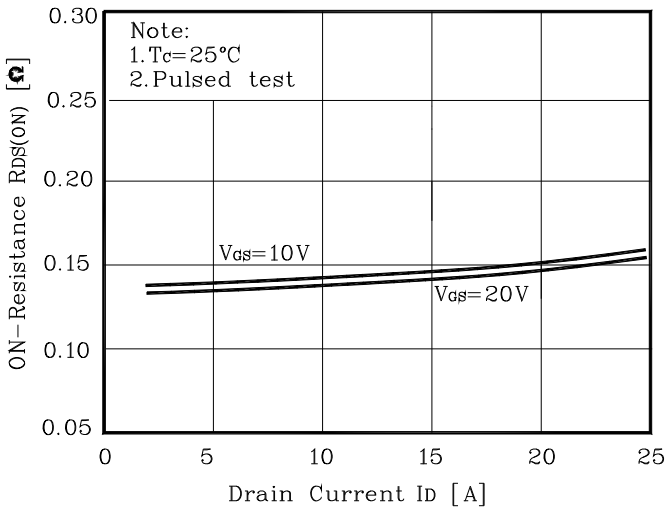
**Fig. 1  $I_D - V_{DS}$**



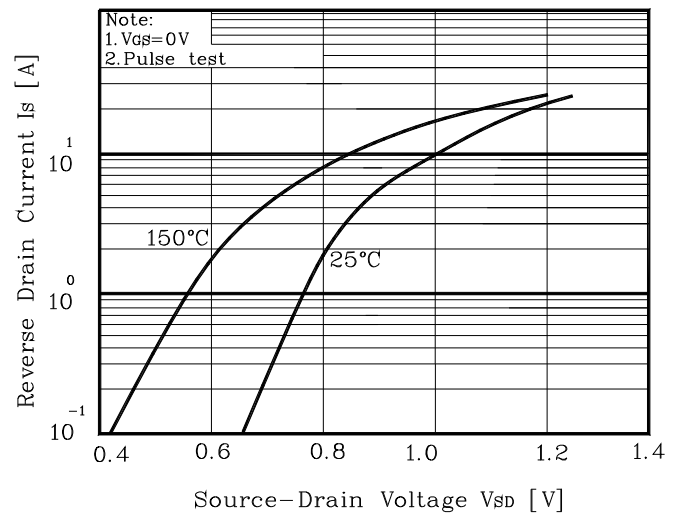
**Fig. 2  $I_D - V_{GS}$**



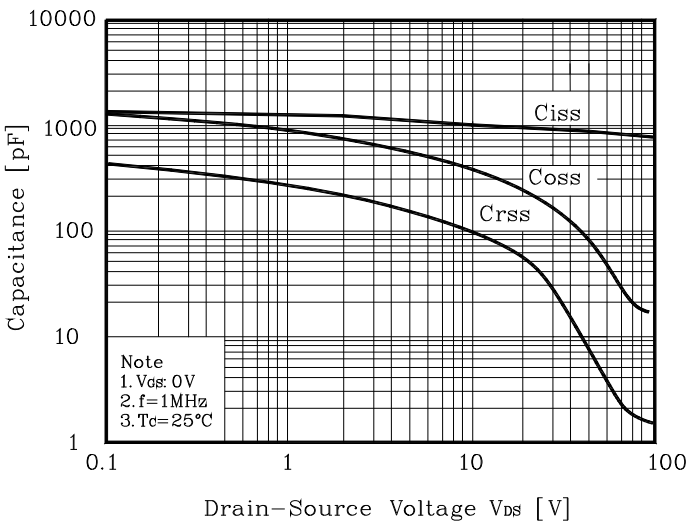
**Fig. 3  $R_{DS(on)} - I_D$**



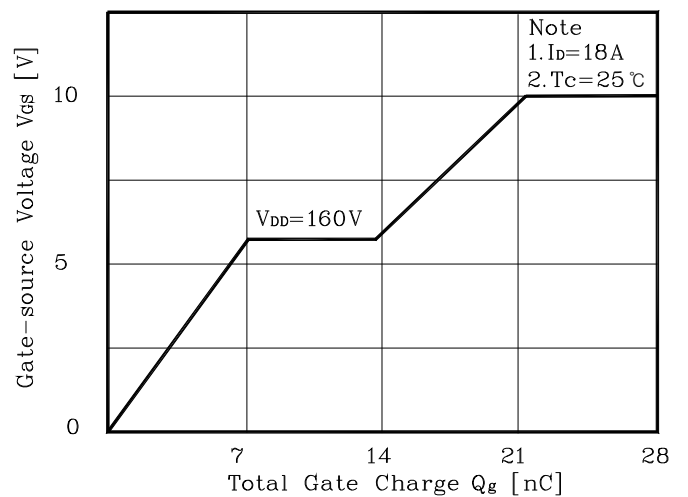
**Fig. 4  $I_S - V_{SD}$**



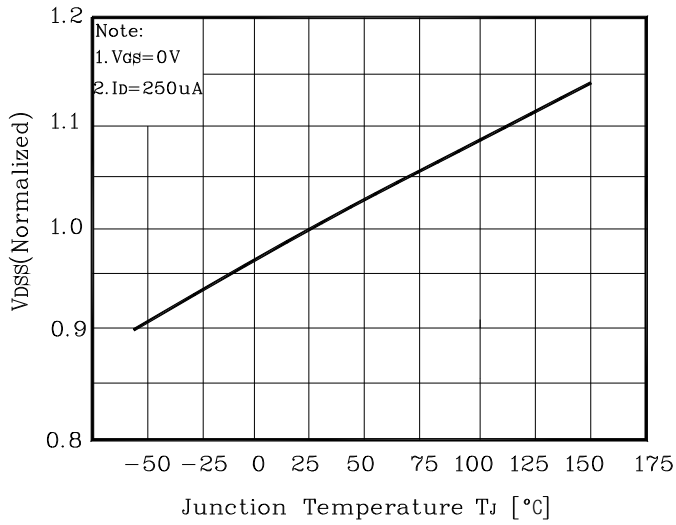
**Fig. 5 Capacitance -  $V_{DS}$**



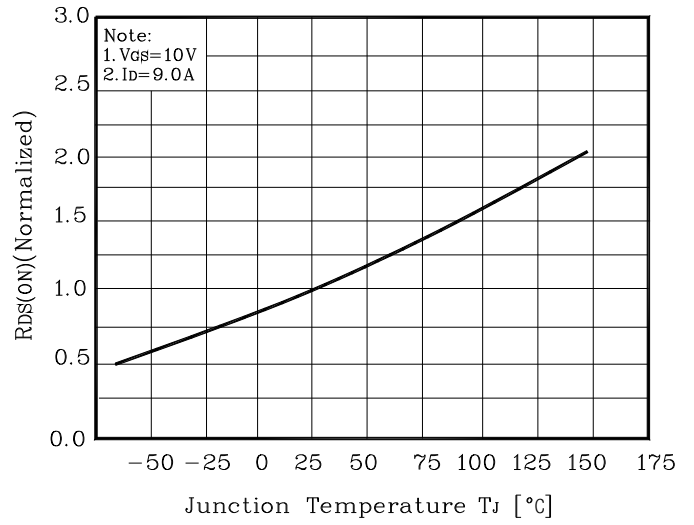
**Fig. 6  $V_{GS} - Q_g$**



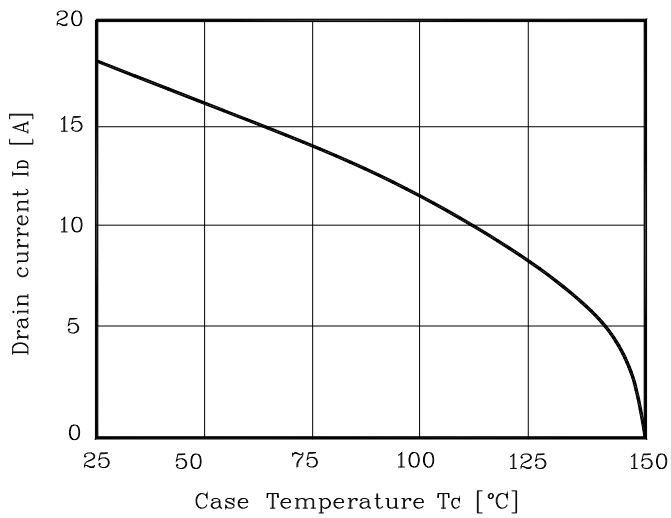
**Fig. 7  $V_{DSS} - T_J$**



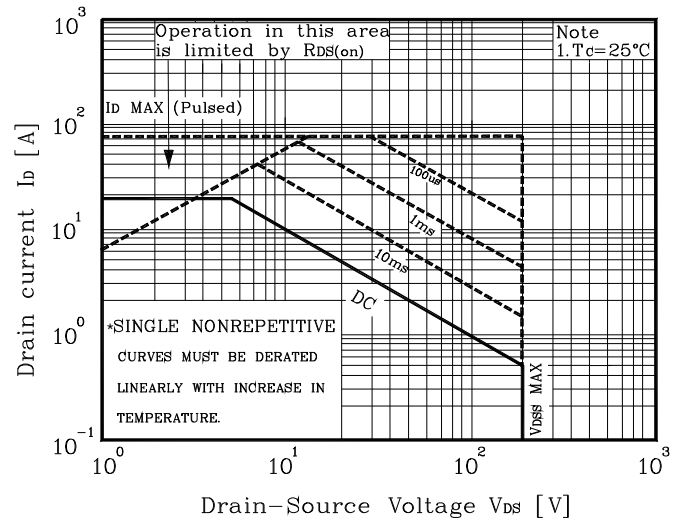
**Fig. 8  $R_{DS(on)} - T_J$**



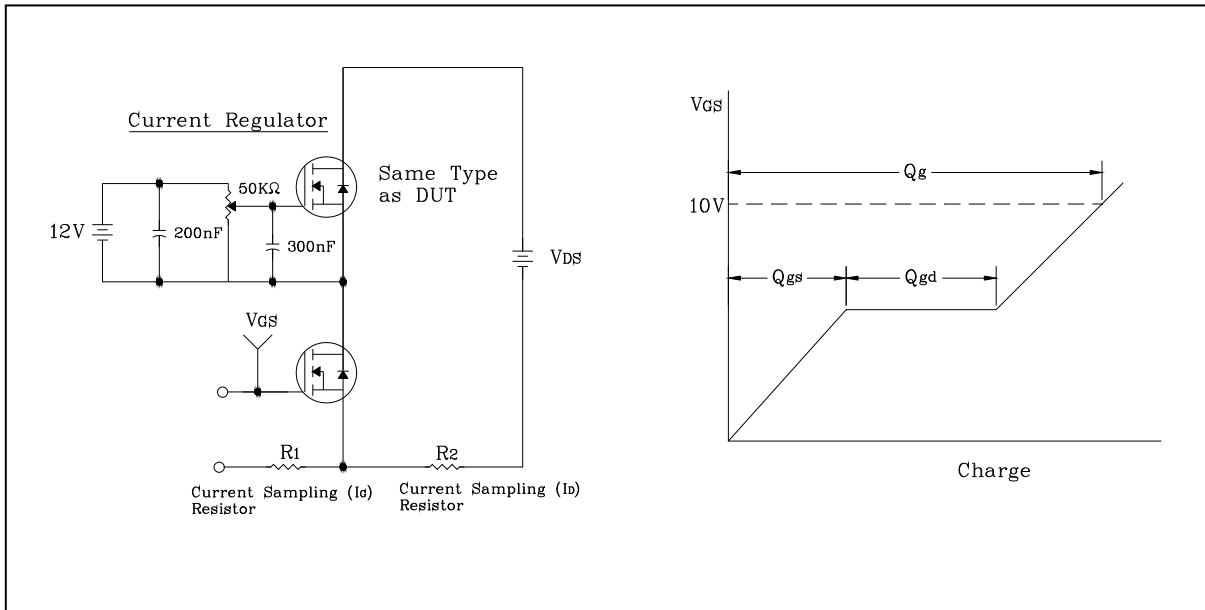
**Fig. 9  $I_D - T_C$**



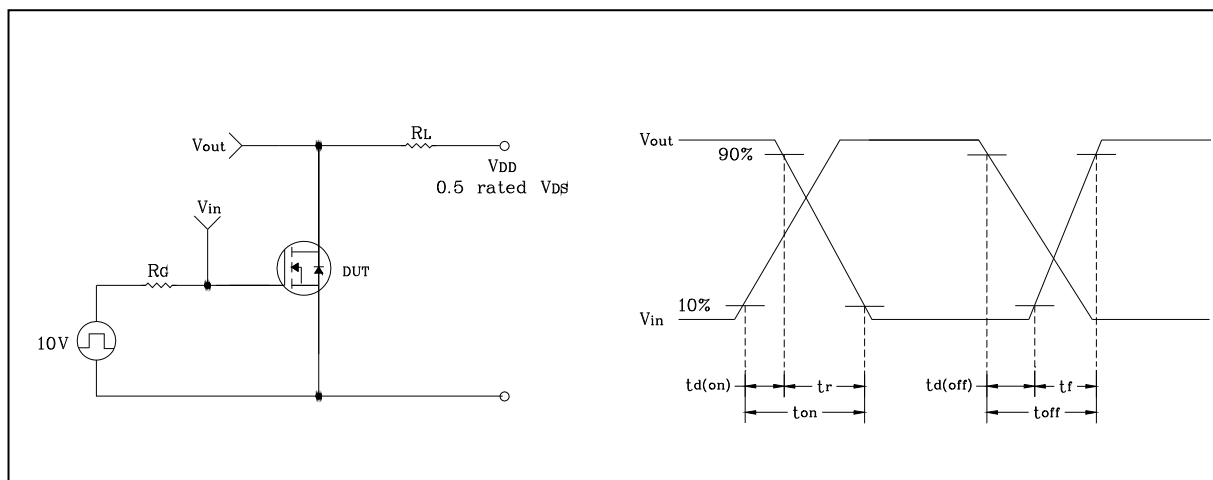
**Fig. 10 Safe Operating Area**



**Fig. 11 Gate Charge Test Circuit & Waveform**



**Fig. 12 Resistive Switching Test Circuit & Waveform**



**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**

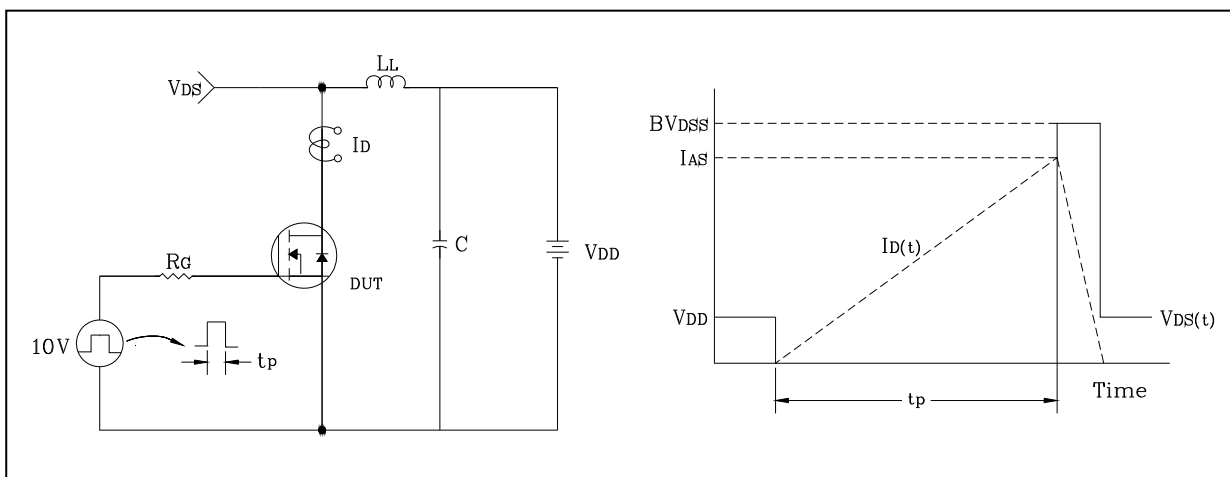
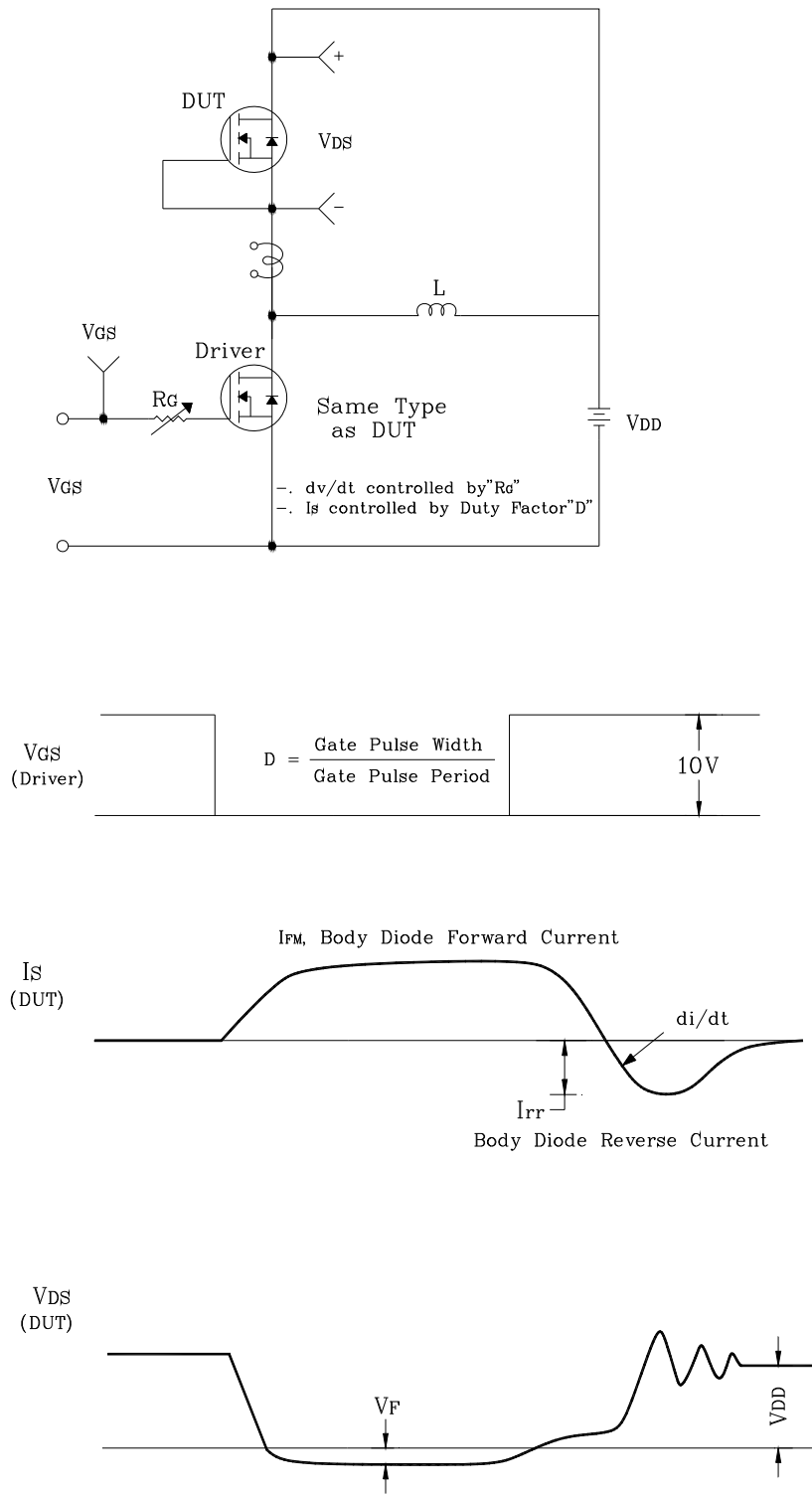
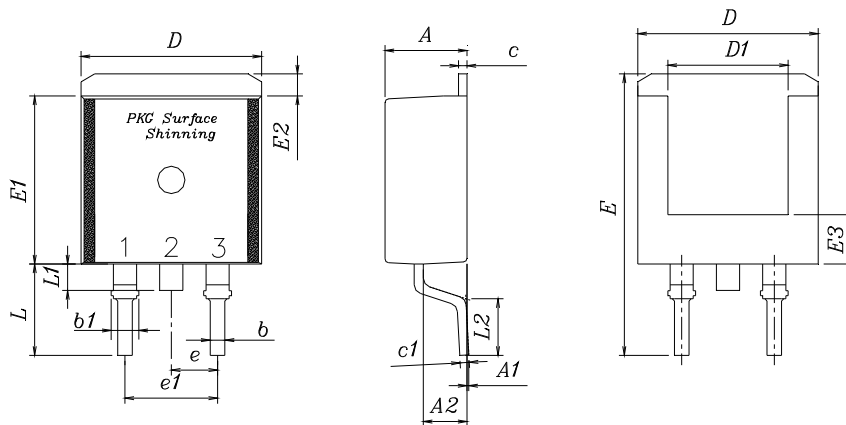


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



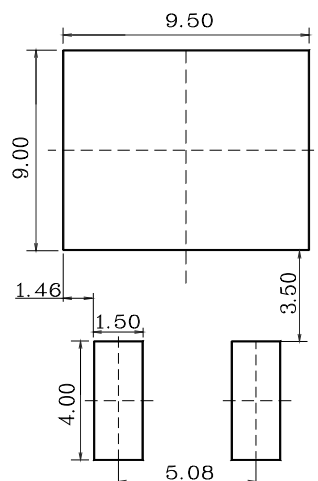
## Outline Dimension

unit: mm



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	4.35	4.50	4.65	
A1	—	—	0.15	
A2	2.20	2.40	2.60	
b	0.70	0.80	0.90	
b1	1.17	1.27	1.37	
c	0.40	0.50	0.60	
c1	0.40	0.50	0.60	
D	9.80	10.00	10.20	
D1	6.40	6.60	6.80	
E	15.00	15.40	15.80	
E1	9.05	9.20	9.35	
E2	1.00	1.20	1.40	
E3	2.50	2.70	2.90	
e	2.34	2.54	2.74	
e1	4.88	5.08	5.28	
L	4.60	5.00	5.40	
L1	1.40	1.45	1.50	
L2	2.50	—	—	

### ※ Recommended Land Pattern [unit: mm]



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